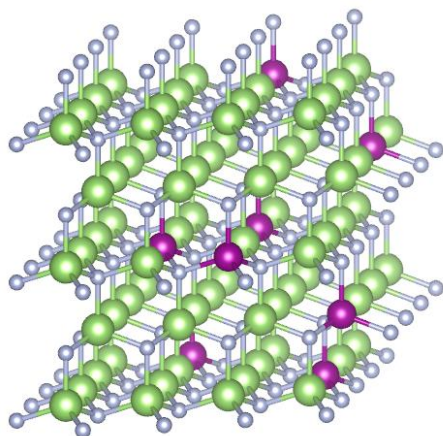


## SEMINARIUM RENTGENOWSKIE

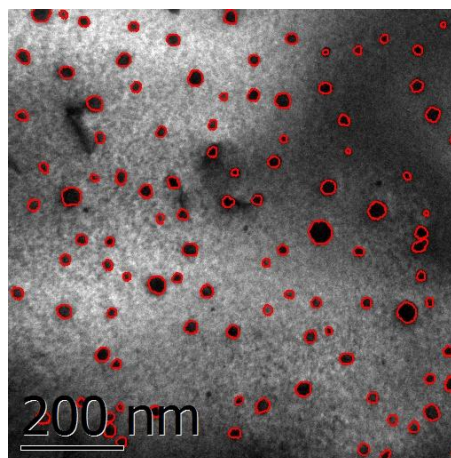
Dnia 03.06.2014r. o godz. 10.30, w Sali D Instytutu Fizyki PAN, odbędzie się seminarium rtg., na którym **dr Tian Li** z Instytutu Fizyki PAN, wygłosi referat na temat:

### "TEM study of transitional-metal doped-semiconductors"

Introduction to transitional-metal (TM) doped-semiconductors is made. As an indispensable characterization technique, transmission electron microscopy (TEM) and its application to study (TM) doped-semiconductors are demonstrated, which include some experimental data and data processing results. Further study on magnetic properties by advanced TEM techniques such as Lorentz microscopy and electron holography are also envisioned.



TM-doped semiconductor



Fe-rich nanocrystals in Fe-doped GaN

dr hab. Sławomir Kret